

Notice of References Cited

Application/Control No.

10/064,317

Applicant(s)/Patent Under
Reexamination
BUNT ET AL.

Examiner

Maria Guerrero

Art Unit

2822

Page 1 of 1

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*	Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
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NON-PATENT DOCUMENTS

*	Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
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*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.